

RLT6530G

Visible Laser Diode

ABSOLUTE MAXIMUM RATINGS ($T_c=25^{\circ}\text{C}$)

Features

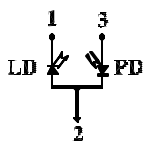
- Index Guided MQW Structure
- Wavelength : 655 nm (Typ.)
- Optical Power : 30 mW CW
- Threshold Current : 50 mA (Typ.)
- Standard Package : 9.0 mm \varnothing

DESCRIPTION	SYMBOL	RATED VALUE
Optical Power (mW)	Po	30
Operation Temperature ($^{\circ}\text{C}$)	Top	-10 to +40
Storage Temperature ($^{\circ}\text{C}$)	Tstg	-40 to +85
LD Reverse Voltage (V)	VLDR	2
PD Reverse Voltage (V)	VPDR	30

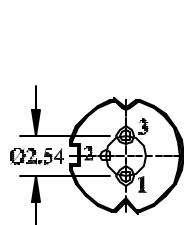
OPTICAL AND ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$)

DESCRIPTION	SYMBOL	MIN.	TYPICAL	MAX.	TEST CONDITION
Lasing Wavelength (nm)	λ_p	645	655	665	Po=30mW
Threshold Current (mA)	Ith	30	50	70	Po=30mW
Operation Current (mA)	Iop	60	80	100	Po=30mW
Operation Voltage (V)	Vop	2.0	2.2	2.7	Po=30mW
Monitor Current (μA)	Im	10	-	-	Po=30mW, VR=5V
Slope Efficiency (mW/mA)	ζ	0.3	0.4	0.7	***
Beam Divergence \downarrow ($^{\circ}$)	θ_{\downarrow}	8	10	11	Po=30mW
Beam Divergence \wedge ($^{\circ}$)	θ_{\wedge}	25	31	40	Po=30mW
Astigmatism (μm)	As	***	11	***	Po=30mW, NA=0.4

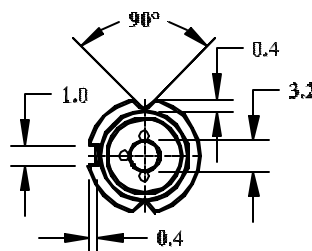
Pin Connection



1. Laser diode cathode
 2. Laser diode anode
 3. Photodiode cathode
- * Case and Pin no. 2 are common



Bottom View



Top View

